Dressed topological edge states in HgTe-based 2D topological insulators

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INTRODUCTION

Enormous efforts are focused on the edge states of two-dimensional topological insulators currently, motivated by exotic fundamental physics, robust topological quantum computation and novel spinorbitronics. Progress is however largely impeded by the fragility of the edge states visible only on short lengths. In this context, microwave transport allows us to capacitively probe the density of states of HgTe topological insulators while measuring simultaneously the device resistance. Besides bulk states, the dynamical transport highlights the responses of the edges, which host very mobile carriers, but are also much denser than theoretically expected. We propose a scenario of ‘dressed’ topological edge states, with topological edge carriers coupled to neighboring confined bulk states. These additional states thus contribute to the large density of states at the edges and may participate to the fragility of topological edge states by causing additional scattering.

RESULTS

Sample geometry and experimental techniques

In this first section, we describe the samples and the admittance measurement setup. The samples are based...
For these devices, the capacitor mesa is defined via a wet bedded in a gold coplanar waveguide (see Fig. 1a and 1b). Made of square capacitors of side \( L \) denoted Trivial. On each layer, we investigated devices provided by a 5 nm (resp. 8 nm) and a predicted gap \( B \). Topological A (resp. B) has a thickness of 10 nm.

The quantum wells are first characterized using standard processes that preserve the high crystalline quality and the high mobility of the epilayer. The contacts and gate are patterned via optical lithography. The gold gate electrode is evaporated on top of a 7 nm-thick HfO\(_2\) insulating layer, grown by low-temperature atomic layer deposition (ALD)\(^{12}\). An ohmic contact is deposited by Au evaporation.

The capacitors are measured in a cryogenic RF probe station at a temperature \( T = 10 \) K, over a wide range of frequency \( f \), using both a lock-in detector \((f < 1 \text{ MHz})\) and vector network analyzer (VNA) in a range 10 MHz < \( f < 20 \text{ GHz} \). Earlier works\(^{20,21,23}\) have demonstrated that the capacitors can be (assuming translation invariance along the transverse direction) described by a distributed RC line of length \( L \), with line capacitance \( C_t \) and resistance \( R_c \), such as the one depicted in Fig. 1d.

In the low-frequency range, measured either with the lock-in amplifier or the VNA (see Methods), the device is equivalent to a capacitor \( C_t = C_t L \). \( C_t \) is the series addition of the geometric capacitance \( C_g \) and the quantum capacitance \( C_q \): \( C_t = C_g + C_q \). The former accounts for the energy cost required to induce a charge across the dielectric barrier, and depends on the electrostatic coupling between the gate electrode and the QW plane. The latter is accounts for the increase of the Fermi energy, which is sizable in low density electron systems. It is simply given by \( C_q = e^2 \rho \), where \( \rho \) is the density of states (DOS), for weakly interacting systems in the limit of zero temperature. One then directly accesses \( C_t \) when measuring the out-of-phase response of the device, with the admittance given by \( Y(\omega) = \omega C_t \). In the low-frequency range, measured either with the lock-in amplifier or the VNA (see Methods), the device is equivalent to a capacitor \( C_t = C_t L \). \( C_t \) is the series addition of the geometric capacitance \( C_g \) and the quantum capacitance \( C_q \): \( C_t = C_g + C_q \).

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complete characterization of the frequency response in regimes where the distributed nature of the HgTe film can be probed.

Low frequency regime

![Graphs of energy spectrum and quantum capacitance](image)

**FIG. 2. Quantum capacitance of HgTe quantum wells:**

(a, c, e) Energy spectrum as function of momentum \( k_y \), as calculated from a \( \mathbf{k} \cdot \mathbf{p} \) model of the three studied samples (Topological A, Topological B and Trivial). The blue lines correspond to the transverse momentum \( k_y \neq 0 \), the light grey lines to the subbands \( k_y = 0 \).

(b, d, f) Quantum capacitance \( c_q \) (per unit area) as function of energy \( \mu \) for the same three samples (for a size of \( L = 10 \mu m \)). The grey line corresponds to the computed value of \( c_q \) given the \( \mathbf{k} \cdot \mathbf{p} \) band structure, the red lines correspond to experimental data.

This paragraph focuses on the low-frequency quantities \( R_0 \) and \( C_L \), and in particular establishes the existence of a 1D density of states in topological samples, as expected due to the presence of topological edge states. Following the above techniques, we compare experimental measurements of the quantum capacitance \( c_q \) as function of energy \( \mu \) with \( \mathbf{k} \cdot \mathbf{p} \) predictions for each type of sample, as presented in Fig.2. For all three samples, the capacitance is low (between 10 and 20 mF m\(^{-2} \)) in the conduction band (\( \mu > 0 \)), and increases quasi-linearly with \( \mu \), as expected for two-dimensional bands with quasi-linear band dispersion. The agreement with \( \mathbf{k} \cdot \mathbf{p} \) calculations is excellent in this regime, provided the value of \( C_{\mathbf{q}} \) is fine tuned (see SI).

In this regime, the quantum capacitance is given by \( c_q = \frac{\mu^2}{4\epsilon_0(\hbar v_F)^2} \) which yields the Fermi velocity \( v_F \approx 0.8 - 1 \times 10^6 \text{ m s}^{-1} \). In the valence band (\( \mu < 0 \)), we observe that \( c_q \) is very high (\( c_q > 40 \text{ mF m}^{-2} \)) as the valence band has a high mass. \( c_q \) is however difficult to extract with high precision in this range, due to the finite value of the geometric capacitance \( C_g \approx 3.9 \text{ mF m}^{-2} \).

In between these two regimes, a minimum is observed in the data. It indicates the gap of the QW, clearly visible in the \( \mathbf{k} \cdot \mathbf{p} \) calculations. For Trivial, the capacitance reaches a very low value, \( c_q < 1 \text{ mF m}^{-2} \) and the QW is strongly depleted, as expected. In Topological A and B, \( c_q \approx 10 \text{ mF m}^{-2} \) in the gap, where QSH edge states should be observed. A modeling as merely one-dimensional edge states yields a quantum capacitance \( c_q \approx 0.2 \text{ nF m}^{-1} \) for the topological edge states. On a \( L = 10 \mu m \) device, it corresponds to a very low areal contribution \( c_q < 0.1 \text{ mF m}^{-2} \), much smaller than the observed minimum. This residual contribution in the gap is thus unlikely to originate solely from the edge states, but more likely from disorder in the bulk bands.

A rough modeling with a gaussian smearing of states, but more likely from disorder in the bulk bands.

In Fig.3, the total resistance \( R_0 \) of Topological A is presented together with the quantum capacitance \( c_q \). In the valence and conduction band, \( R_0 \) is very low as the QW is very conductive, and saturates close to the value of the contact resistance, \( R_0 \approx R_c \) (the latter being extracted from the high-frequency analysis, and depicted as the dashed line). The gap is clearly indicated by a sharp peak in \( R_0 \). For trivial samples (not shown), the gap is quite insulating and \( R_0 > 400 \text{ k}\Omega \). For topological samples in an ideal QSH regime, the geometry resembles that of a mesoscopic capacitor \( C_{\mathbf{QW}} \), and a charge relaxation resistance between \( R_K \) (coherent regime) and \( R_K \) (incoherent regime) is expected \( \frac{R_K}{R} \) where \( R_K = \hbar / 2 e \) is the resistance quantum. Though many measured peak resistances lie in this range (see Fig.3), none of the samples however exhibit a clear quantized resistance plateau, and higher values \( \sim R_K \) are sometimes reached, probably due to the presence of scattering as the perimeters of the sample are large (30 μm here). Importantly, we find that in all samples the minimum of \( c_q \) and the maximum of \( R_0 \) are not aligned. This indicates that the gap hosts a large amount of bulk states that do not participate very efficiently to transport, and that the Fermi energy is mostly pinned to the valence band. In contrast, the minimum of \( c_q \) (here around \( \mu \approx 10 \text{ meV} \)) corresponds
FIG. 3. Quantum capacitance and resistance of a topological HgTe quantum well: The quantum capacitance per unit area $c_q$ (blue line, left axis) and the total resistance $R_t$ (red line, right axis) are plotted as a function of energy $\mu$. As a grey line, the computed value of $c_q$ given the $k \cdot p$ band structure is also reproduced. As a dashed red line, the contact resistance $R_c$ is plotted in the energy range in which it can meaningfully be extracted from the high-frequency analysis. This dataset has been measured on Topological A for $L = 10 \mu$m.

to a smaller DOS, but a higher conductance.

So far, neither the quantum capacitance $c_q$ nor the resistance $R_t$ enable to directly identify the topological edge states. In the low-frequency regime, an additional parameter such as the dependence on length $L$ is necessary. As a matter of fact, the contributions to the quantum capacitance should scale as $\propto L$ for one-dimensional edge states while two-dimensional bulk bands scale as $\propto L^2$, so that the areal quantum capacitance can be written as (see Methods):

$$c_q = c_{q}^{\text{2D}} + \frac{3c_{q}^{\text{1D}}}{L}$$

with $c_{q}^{\text{1D}}$ and $c_{q}^{\text{2D}}$ the line and surface quantum capacitance. Varying $L$, we now investigate these scaling laws in Fig.4a, 4b, 4c. For Topological A and B all curves are superimposed for $\mu > 60$ meV signaling that $c_q$ does not depend on $L$, and the system is thus two-dimensional. However, a clear length dependence appears for lower energies (Fig.4d and 4e). We observe that the quantum capacitance $c_q$ can be written as the sum of a one-dimensional and a two-dimensional contribution. Fits of the data (see SI) for each $\mu$ finally yield $c_{q}^{\text{1D}}$ and $c_{q}^{\text{2D}}$, plotted in Fig.4b and 4c. The two-dimensional part $c_{q}^{\text{2D}}$ follows the $k \cdot p$ calculations, confirming the validity of the modeling. In contrast, the one-dimensional contribution $c_{q}^{\text{1D}}$ appears at energies $\mu < 40$ meV and is at its largest near the gap. The order of magnitude $c_{q}^{\text{1D}} \approx \frac{5 - 10 \text{nF} \cdot \text{m}^{-1}}{50}$ is however 25 to 50 times larger than that expected for a merely one-dimensional edge (typ. $0.2 \text{nF} \cdot \text{m}^{-1}$). We discuss possible origins in Section Discussion. In contrast, the Trivial sample does not show any clear linear one-dimensional contribution, confirming the absence of edge transport in the gap (Fig.4a and 4b). We however note the scaling analysis can hardly be performed for negative energies. Indeed, $c_q$ varies abruptly, and errors and variations in the determination of $C_g$ are amplified in this regime especially for Trivial as the QW is strongly depleted in the gap.

After identifying the presence of a one-dimensional quantum capacitance $c_{q}^{\text{1D}}$ near the gap of the QW from the length dependence of $C_q$, we now turn to the study of the full high-frequency spectrum of the complex admittance $Y(\omega)$. As the characteristic RC timescales of the one- and two-dimensional components differ, we show below that we can distinguish their respective signatures in this high-frequency regime. Indeed, near the gap of topological samples, the microwave spectrums exhibit striking two-mode dynamical transport which strongly departs from that of a single distributed RC line.

**High frequency regime**

Using a VNA and standard de-embedding techniques (see Methods), we have measured the complex admittance $Y(\omega)$ of the capacitors up to frequencies largely exceeding the charge relaxation frequency $1/2\pi R_C$ of the device, typically $1 \text{GHz}$ for $L = 10 \mu$m. In this high-frequency regime, propagation effects cannot be neglected, and the capacitors host evanescent waves, driven by the resistance of the HgTe film. Assuming translation invariance along the transverse axis, the admittance of the capacitor reads (see SI):

$$Y(\omega) = \frac{1}{1/R_c + \frac{1}{\pi} \tanh (ik)}$$

where $R_c$ describes the lumped contact resistance, while the tanh term describes the evanescent waves in the capacitor with $k = \sqrt{1/RC}(\omega)$. The fits obtained with this simple model yields an excellent agreement in a wide range of energies corresponding mostly to the valence and conduction band as illustrated in Fig.4 and 5. The low frequency part (Fig.5a) in particular validates the expansion used in the low-frequency regime. The high frequency regime confirms the evanescent regime, and yields the value of the HgTe sheet resistance $R$ and of the contact resistance $R_c$. $R_c$ is found to be relatively independent of $V_g$ in the validity range of the model, with $R_c = 0.3 - 4 \text{k}\Omega$ depending on sample, slightly higher for non-inverted than for topological samples. However, in Topological A and B, we observe strong discrepancies arising near the gap between this simple one-carrier model and the data as illustrated in Fig.5b and 5c. In particular, the admittance $Y$ exhibits two successive low-frequency regimes (DC-$0.2 \text{GHz}$ and $0.2-0.8 \text{GHz}$). We attribute these features to the presence of two independent types of charge carriers, namely the bulk (2D) and edge (1D carries), in
FIG. 4. Length dependence of the quantum capacitance: a, b, c) Quantum capacitance $c_q$ (per unit area) as function of energy $\mu$ measured for different lengths $L = 3, 5, 10, 20\mu m$. The grey line corresponds to the computed value of $c_q$ given the $k \cdot p$ band structure, the colored lines correspond to experimental data for a size $L$ indicated by the caption d, e, f) On the left axis, two-dimensional component $c_{q2D}$ (per unit area) as a blue line, the grey line corresponds to $c_q$ computed from the $k \cdot p$ band structure. On the right axis, one-dimensional component $c_{q1D}$ (per unit length) as a red line.

accordance with the results of the low-frequency analysis, with different charge relaxation times. Consequently, we model the system using two parallel distinct distributed RC circuits, each with a contact resistance:

$$Y(\omega) = Y^{1D}(\omega) + Y^{2D}(\omega)$$

where $Y^{1D/2D}$ are both given by Eq.(2). We obtain an excellent agreement between model and data over the full frequency range (Fig.5c and 5d) and the two low-frequency regimes are fully captured. However the fits can efficiently be performed only in a small region of energies, for which the two circuits are sufficiently distinguishable. The results are shown in Fig.6a. The largest contribution $c_{q2D}$ is attributed to the two-dimensional bulk states and is observed to follow the $k \cdot p$ predictions. Additionally the small contribution of the second carrier is observed to grow close to the gap is consequently attributed to $c_{q1D}$. Its order of magnitude in the gap $c_{q1D} \approx 10$ nF m$^{-1}$ is compatible with the results obtained from the low-frequency length dependence, thus validating our analysis. Our measurement technique is primarily sensitive to capacitances. Consequently, though the contact and sheet resistances can easily be separated in the single-carrier model, they can only be determined with an accuracy of typically 50% in the two-carrier model.

We observe nonetheless that, near the gap, the total 2D resistance $R^{2D} \approx 40$ kΩ is much larger than the total 1D resistance $R^{1D} \approx 10 - 15$ kΩ. Moreover, the analysis gives access to the charge relaxation times and frequencies (given respectively by $\tau_{1D/2D} = R_{1D/2D} c_{1D/2D}$ and $f_{1D/2D} = 1/2\pi \tau_{1D/2D}$), as plotted in Fig.6b. In the conduction band, where the single-mode picture holds, we observe that the (bulk) electrons have a short charge relaxation time ($\tau_{2D} \approx 0.23$ ns) or equivalently a high response frequency ($f_{2D} \approx 0.7$ GHz). However, this charge relaxation time increases drastically when the Fermi level approaches the gap and reaches $\tau_{2D} \approx 1.5$ ns ($f_{2D} \approx 0.1$ GHz). In the same energy range, the second contribution, attributed to the edge electrons, yields a short response time $\tau_{1D} \approx 0.17$ ns ($f_{1D} \approx 0.9$ GHz).

Together, the analysis of the capacitances and charge relaxation times substantiates and sharpens the picture obtained in the low-frequency regime near the gap, with a small edge DOS with ‘fast’ electrons and rather high conductance, atop a very dense but resistive and ‘slow’ bulk background. In the last section, we summarize the results obtained from both the low- and high-frequency methods and discuss their outreach in the perspective of improving the transport quality of topological edge states.
FIG. 5. High-frequency admittance: Admittance $Y$ as function of frequency $f$ in the DC – 3 GHz for different energies $\mu$, obtained on sample Topological B for $L = 5 \mu$m. The value of $\mu$ is indicated in each panel. Panels a,b correspond to the conduction band, h and i to the valence band, and show a good agreement with a single-mode model. The other panels (c, d, e, f, g) correspond to the transition from valence to conduction bands, according to the band structure in Fig.6. They exhibit a different spectrum, with two low-frequency regimes, and are only well fitted by the two-mode model. The best fits (either single- or two-mode) are shown as a grey line in all panels. The vertical dashed lines indicate the values of the charge relaxation frequencies $f_{2D}$, and $f_{1D}$ (when in the frequency range, panels e, f, g).

**DISCUSSION**

The study of capacitors unveils a precise and surprising description of the density of states in the two-dimensional topological insulator HgTe. A one-dimensional component can be detected near the gap of the QW only in inverted (topological) heterostructures, so that it is thus likely to originate from the topological edge states. This one-dimensional DOS coexists with the conduction band over a large range of energies (roughly 50 meV), in line with theoretical predictions and observations. However it is partially obscured by the very large DOS of the two-dimensional bulk when approaching the gap. In fact, in topological samples (such as Topological A and B), the gap is clearly indicated by a maximum in the resistance $R_t$, but corresponds to a large DOS, whereas the minimum in the DOS is often located above the gap ($\mu \simeq 5 - 10 \mu$eV). This configuration is likely to be the result of disorder or inhomogeneous electrostatics in the samples, yielding charge puddles which pin the Fermi energy in the valence bands, and smear out the very heavy valence band over an energy scale of 10 to 30 meV. The bulk is, as expected, found to be rather resistive in the gap. It may still however influence the conductance, for example in Josephson junctions for which the aspect ratio favors it. Hence, our observations explain a posteriori why the fractional Josephson effect in HgTe has been observed to be stronger in the conduction band than in the gap. As this very large two-dimensional DOS near the gap directly results from the very heavy valence band, band structure engineering as tested on HgTe may help reducing the amount of states in the bulk.
be the result of disorder, especially when the gap of the QW is small. The puddles have been suggested as a potential source of scattering and could be identified via specific signatures in the noise. However, Eq. (1) assumes a uniform puddle density and thus strongly suggests that the charge density is larger close to the edges of the sample. Gate electrostatics could play an important role and enhance the creation of electron pockets confined near the edges as the topological edge states themselves may screen the action of the gate. Regardless of the microscopic details, one can estimate that a (spin-degenerate) bulk sub-band, could contribute up to 5 nF m$^{-1}$, so that typically 1 to 2 states would reside in the vicinity of the topological edge states.

Finally, we point out that very dissimilar time-scales rule the electronic transport of the one- and two-dimensional states near the gap regions, with charge relaxation times such that $\tau_{2D} \approx 9 \tau_{1D}$. This suggests that a careful choice of the drive frequency would allow for addressing dynamically the edge states on time-scales over which the bulk states are frozen. Our results confirms the interest of microwaves for investigating the physics of topological edge states, and in particular the peculiar Luttinger liquid behavior which is more naturally unveiled at finite frequencies.

In a nutshell, our measurements bring up new information on the microscopic details of topological edge states. While the bulk is mostly insulating in the gap, its DOS is very large and may obscure that of the edges. Most strikingly, the edge states are found to be rather dense which suggests that they consist of topological edge states dressed by other states, which contribute to the large DOS and to scattering, but not in a significant manner to transport. This scenario highlights the interplay of charge disorder and gate electrostatics with the physics of edge states, and is inherent to the physics of QSH edge states.

Thus, this work opens new directions in the search for robust topological systems, for example the development of lateral gates to control the electrostatic potential near the edges, or the dynamical addressing of the edge states. We also believe that our observations call for in-depth theoretical modeling of QSH edges. The idealized homogeneous insulating bulk is hardly achieved in practice in a topological insulator, which calls for an electrostatic model of the bulk and edge states as a prerequisite robust topological edges states suitable for topological quantum computation or spinorbitronics.

**METHODS**

**Experimental techniques**

The measurements have been performed in a microwave cryogenic probe station Janis ST-500 equipped with Picoprobe GSG-100 microwave probes. The low-frequency measurements rely on a lock-in detector (Zurich Instruments HF2LI) combined with a low-noise ac modulator and a lock-in amplifier (Zurich Instruments SMI2000). The measurements have been performed in a microwave cryogenic probe station Janis ST-500 equipped with Picoprobe GSG-100 microwave probes. The low-frequency measurements rely on a lock-in detector (Zurich Instruments HF2LI) combined with a low-noise ac modulator and a lock-in amplifier (Zurich Instruments SMI2000).
pre-amplifier. For high-frequency phase-referenced measurements, we use a Vector Network Analyzer (VNA) Anritsu MS4640. The VNA is first calibrated in the desired frequency range using the SOLT (short-open-load-thru) method on a calibration substrate Picoprobe CS5, thus moving the reference planes to the microwave probe ends. The propagation in the contacts is further corrected by measuring the response of a thru-line. Finally, stray capacitances are subtracted by measuring a dummy device with identical geometry but without the conductive HgTe mesa structure.

Length dependence

When in the gap, the quantum capacitance $c_q$ exhibits a length dependence, suggesting that the surface (total surface $S_t = L^2$) is split in two parts:

- the edges, surface $S_1 = 3WL - 2W^2 \simeq 3WL$
- the bulk, surface $S_2 = (L - W)(L - 2W) = S_1 - S_1$

where $W$ is the width of the edge states. The edge states are assumed to run on three sides only of the gated surface $L^2$, but not on the side nearby the contact. We assume a geometric capacitance $C_q = c_q L^2$, in series with the two quantum capacitances $c_q S_1$ and $c_q S_2$ in parallel:

$$C_q = c_q S_1 + c_q S_2$$

$$= 2c_q^2 L^2 + 3c_q^2 L$$

These expressions can be used to compute $c_q^2$ and $c_q^1$ in the two-carrier model.

DATA AVAILABILITY

The data sets generated and/or analyzed during the current study are available from the corresponding author on reasonable request.

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AUTHOR CONTRIBUTIONS

M.C.D., S.H., A.G. and H.Ba. performed the measurements. S.H. and K.B. fabricated the samples, based on MBE layers grown by R.S. and L.L. E.B. supervised the project. All authors participated to the analysis of the results and to the writing of the manuscript.

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Supplementary Online Material

I. FROM $C_t$ TO $c_q$

The measurements with a lock-in amplifier or a VNA directly yields the total capacitance $C_t$ of the sample. An example measurement of $C_t$ as function of $V_g$ is shown in Fig.7a. The gap feature is immediately visible around $V_g \simeq 0.1$ V as a dip in $C_t$. The contrast is very good (typically 25 % modulation of $C_t$) thanks to the very thin insulator layer that maximizes the value of $C_t$. A clear saturation is observed for $V_g < -0.2$ V that signals the very heavy valence band, for which $C_t \simeq C_g$. From the saturation value, we obtain $C_g$ with an estimated error $< 2\%$. Knowing $C_g$, we compute $C_q$ and $c_q = C_q S$, where $S$ is the area of the sample. To avoid any systematic error in $c_q$, we measure $S$ with microscope pictures. In the length dependence (see Main article), we use $\sqrt{S}$ rather than the nominal value $L$. Despite the accuracy of less than 2% on $C_g$, the agreement with $k \cdot p$ prediction can sometimes be mediocre. For simplicity, we take these theoretical predictions as a reference and thus fine tune the value of $C_g$ (within 2%) to obtain the best agreement, and finally obtain the plot of $c_q$ as function of $\mu$ as presented in Fig.7.

II. HIGH FREQUENCY ADMITTANCE

Following earlier works, we model the capacitor as a distributed RC line (of length $L$ along the $x$ axis, see Main text). On the source side, an oscillating voltage $V_{ac}(t)$ is applied, while a dc gate voltage is set to the other end of the line. Solving the Kirchhoff equations, one can easily show that the local voltage $V(x)$ and current $I(x)$ read:

$$V(x) = V_e e^{i \gamma x} + V_- e^{-i \gamma x}$$

(8)

$$I(x) = \frac{i \gamma}{r} (V_+ e^{i \gamma x} + V_- e^{-i \gamma x})$$

(9)

with $\gamma = \sqrt{i \omega R C_t}$. Solving for the above mentioned boundary conditions, this immediately yields the admittance $Y_0(\omega)$ of the line:

$$Y_0(\omega) = \frac{I(0)}{V(0)} = \frac{i \gamma}{r} \tanh(i \gamma L) = \frac{i k}{R} \tanh(ik)$$

(10)

with $k = \sqrt{i \omega R C_t}$, $R = R_L C_t = C_t L$. Taking into account the contact resistance between the QW and the gold lead of the source, a discrete resistance $R_c$ is further attached to one end and the admittance $Y$ is finally given by:

$$Y(\omega) = \frac{1}{1/R_0 + Y_0(\omega)} = \frac{1}{1/R_c + \frac{1}{R_c} \tanh(ik)}$$

(11)

The low frequency expansion of $Y(\omega)$ can then be calculated, and gives:

$$Y(\omega) = i \omega C + \omega^2 R_0 C^2 + o(\omega^2)$$

(12)

with $R_0 = R_c + \frac{R_s}{2}$.

III. EXAMPLE RF SPECTRUM

In this section, we show how the single-mode model fails to describe the spectra measured near the gap. In Fig.8, we first present data taken in the conduction band (Fig.8a and 8b), showing perfect agreement with the single-mode fit. In Fig.8c and 8d, the single-mode fit fails to describe data taken near the gap (dashed line) while a two-mode fit accounts for the observation of two distinct charge relaxation times.
FIG. 7. Quantum capacitances of the two electron systems: On the left axis, the total quantum capacitance $C_q$ is plotted in blue. The capacitance of the largest electron system $C_{q2D}^\text{2D}$ attributed to the 2D bulk carriers, is shown alongside in purple. The prediction of the $k \cdot p$ calculations are shown as a solid grey line.

FIG. 8. Microwave admittance: a,b) Microwave admittance $Y$ as function of frequency $f$ measured in the conduction band shown as blue and red dots, showing a very good agreement with the single-mode model (shown as a dark grey line) c,d) Microwave admittance $Y$ as function of frequency $f$ measured near the gap. It shows a very good agreement with the two-mode model (shown as a dark grey line), while the single-mode model fails to reproduce the observed behaviors (dashed lines).